

Diode al Silicio

Variable Capacitance Silicon Epitaxial Planar Diodes in DO-35 glass case for TV and FM tuners

Type	Characteristics @ $T_{amb} = 25\text{ }^\circ\text{C}$								
	Capacitance @ $V_R = 3\text{ V}$		Capacitance ratio @ $V_R = 3 \dots 25\text{ V}$	Series resistance @ $C_{tot} = 9\text{ pF}$ $f = 470\text{ MHz}$ [12 pF, 330 MHz]	Cutoff frequency for $Q = 1$ @ $V_R = 3\text{ V}$	Series inductance at 1.5 mm distance from package	Series resonance frequency @ $V_R = 25\text{ V}$	Leakage current @ $V_R = 28\text{ V}$	Breakdown voltage @ $I_R = 100\text{ }\mu\text{A}$
	$C_{tot}\text{ pF}$	$C_{tot}\text{ pF}$							
			$C_{tot}\text{ (3 V)}$ $C_{tot}\text{ (25 V)}$	$r_s\text{ }\Omega$	$f_{Q1}\text{ GHz}$	$L_s\text{ nH}$	$f_0\text{ GHz}$	$I_R\text{ nA}$	$V_{(BR)R}\text{ V}$
BB 121 A	11	2,0 ... 2,35	4,5 ... 6	0,6 (< 0,8)	24	2,5	2	< 50	> 30
BB 121 B	12	2,25 ... 2,65	4,5 ... 6	0,6 (< 0,8)	24	2,5	2	< 50	> 30
BB 122	13	2,0 ... 2,8	4,5 ... 6	0,9 (< 1,2)	16	2,5	1,8	< 50	> 30
BB 139	29	4,3 ... 6	5 ... 6,5	0,5	14	2,5	1,4	< 50	> 30
BB 141 A	11	2,0 ... 2,35	4 ... 6	0,6 (< 0,8)	24	2,5	2	< 50	> 30
BB 141 B	13	2,25 ... 2,65	4 ... 6	0,6 (< 0,8)	24	2,5	2	< 50	> 30
BB 142	12	2,0 ... 3,0	4 ... 6	0,9 (< 1,2)	16	2,5	1,8	< 50	> 30
BB 221	11	1,8 ... 2,2	5 ... 6	0,6 (< 0,8)	24	2,5	2	< 50	> 30
BB 222	11	1,8 ... 2,6	4,3 ... 6	0,9 (< 1,2)	16	2,5	1,8	< 50	> 30
BB 229	21	2,6 ... 3	> 6,8	[0,85]	9	2,5	1,9	< 50	> 30

These diodes are available in matched sets for radio, TV, UHF, and VHF tuners. For matching conditions see data book.

Silicon Epitaxial Planar Diode Switches in DO-35 glass case for electronic bandswitching in radio and TV tuners

Type	Maximum Ratings			Characteristics @ $T_{amb} = 25\text{ }^\circ\text{C}$						
	Reverse voltage $V_R\text{ V}$	Forward current @ $T_{amb} = 60\text{ }^\circ\text{C}$ $I_F\text{ mA}$	Junction temperature $T_j\text{ }^\circ\text{C}$	Forward voltage @ $I_F = 100\text{ mA}$ $V_F\text{ V}$	Leakage current @ $V_R = 15\text{ V}$ $I_R\text{ nA}$	Series inductance across the package $L_s\text{ nH}$	Dynamic forward resistance dynamic $I_F = 10\text{ mA}$, $f = 50 \dots 1000\text{ MHz}$ $r_f\text{ }\Omega$	Relative variation of the diff. forward resistance with the forward current in the range of $I_F = 2 \dots 40\text{ mA}$ %/mA	Capacitance @ $f = 1\text{ MHz}$ $C_{tot}\text{ pF}$	@ $V_R\text{ V}$
BA 243	20	100	150	< 1	< 100	2,5	0,7 (< 1)	5	< 2	15
BA 244	20	100	150	< 1	< 100	2,5	0,4 (< 0,5)	5	< 2	15
BA 243 A	20	100	150	< 1	< 100	2,5	0,7 (< 1)	5	< 1	20
BA 244 A (\cong BA 182)	20	100	150	< 1	< 100	2,5	0,4 (< 0,5)	5	< 1	20

Silicon PIN Diodes in 50 B 4 plastic case

PIN diode π network for electronic amplitude control in TV tuners and antenna branching amplifiers.

Type	Maximum Ratings of individual diodes			Characteristics of individual diodes @ $T_{amb} = 25\text{ }^\circ\text{C}$				Characteristics of π network @ $T_{amb} = 25\text{ }^\circ\text{C}$		
	Reverse voltage $V_R\text{ V}$	Forward current @ $T_{amb} = 25\text{ }^\circ\text{C}$ $I_F\text{ mA}$	Junction temperature $T_j\text{ }^\circ\text{C}$	Forward voltage @ $I_F = 50\text{ mA}$ $V_F\text{ V}$	Reverse current @ $V_R = 15\text{ V}$ $I_R\text{ nA}$	differential forward resistance @ $f = 100\text{ MHz}$ @ $I_F = 10\text{ mA}$ @ $I_F = 10\text{ }\mu\text{A}$ $r_f\text{ }\Omega$ $r_f\text{ }\Omega$		Attenuation in the range of 40 ... 1000 MHz @ $V_{co} = 1,5\text{ V}$ @ $V_{co} = 5\text{ V}$ $\alpha_{max}\text{ dB}$ $\alpha_{min}\text{ dB}$	Voltage for 1 % cross modulation $V_{cr}\text{ V}$	
TDA 1053	30	50	125	< 1,2	< 500	5	1400	45 (> 36)	1,5 (< 2)	1

Diodi Emittitori di Luce - Diodi al Germanio

Light Emitting Diodes in plastic case

Light emitting diodes for general purpose use in modern electronic systems (socket C 65 see page 54)

Type	Maximum Ratings			Characteristics @ $T_{amb} = 25^\circ C$						
	Forward current	Reverse voltage	Power dissipation @ $T_{amb} = 25^\circ C$	Colour	Forward voltage @ $I_F = 20\text{ mA}$	Breakdown voltage @ $I_R = 10\ \mu A$	Luminous area	Luminous intensity @ $I_F = 20\text{ mA}$	Luminous flux @ $I_F = 20\text{ mA}$	Wavelength @ peak emission, $I_F = 20\text{ mA}$
	$I_F\text{ mA}$	$V_R\text{ V}$	$P_{tot}\text{ mW}$		$V_F\text{ V}$	$V_{(BR)R}\text{ V}$	$F\text{ mm}^2$	$I\text{ mcd}$	$\Phi\text{ mlm}$	$\lambda_{pk}\text{ nm}$
CQY 65	100	3	210	red	1,65 (< 2)	20 (> 3)	7	1,5 (> 0,5)	0,8	650
CQY 66	60	3	210	green	2,5 (< 3,3)	20 (> 3)	7	1,5 (> 0,5)	0,8	565
CQY 67	60	3	210	yellow	2,5 (< 3,3)	20 (> 3)	7	1,5 (> 0,5)	0,8	585

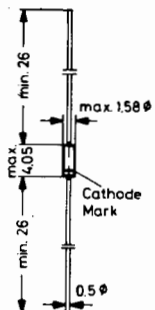
Germanium Gold Bonded Diodes in DO-7 glass case

The AA 143 is particularly suited for ratio detector and discriminator circuits.

Type	Maximum Ratings			Characteristics @ $T_{amb} = 25^\circ C$				
	Reverse voltage	DC current half wave rect. with resistive load @ $T_{amb} = 25^\circ C$	Power dissipation @ $T_{amb} = 25^\circ C$	Junction temperature	Forward voltage		Leakage current	
	$V_R\text{ V}$	$I_0\text{ mA}$	$P_{tot}\text{ mW}$	$T_j\text{ }^\circ C$	$V_F\text{ V}$	@ $I_F\text{ mA}$	$I_R\ \mu A$	@ $V_R\text{ V}$
AA 143	25	60	80	85	0,29 ... 0,33	2	< 20	20
AA 144	90	10	80	85	0,36 (< 1)	5	< 200	75

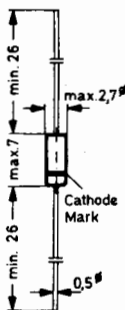
DO-35 glass case

54 A 2 according to DIN 41 880
Weight approx. 0.13 g



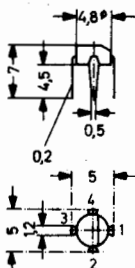
DO-7 glass case

51 A 2 according to DIN 41 880
Weight approx. 0.2 g



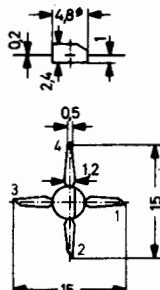
Plastic package 50 B 4

according to DIN 41 867
with vertical leads
Weight approx. 0.1 g



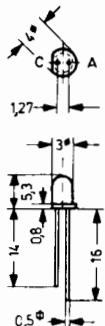
Plastic package 50 B 4

according to DIN 41 867
with horizontal leads
Weight approx. 0.1 g



CQY 65 ... 67

Plastic case
Weight approx. 0.1 g



Dimensions in mm